## Universal Hall mobility in *c*-axis-oriented $Y_{0.5}Ca_{0.5}Ba_2Cu_3O_{7-\delta}$ thin films

H. Yakabe,\* I. Terasaki, M. Kosuge,† Y. Shiohara, and N. Koshizuka

Superconductivity Research Laboratory, 10-13 Shinonome 1-chome, Koto-ku, Tokyo, 135 Japan

(Received 26 August 1996)

Transport properties of *c*-axis-oriented  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films with a wide range of x=0-0.5 and  $\delta=0.08-1.0$  have been systematically investigated. Hall mobility  $\mu_H$  in all the films satisfies the relation of  $\mu_H^{-1} = \alpha T^2 + C$  ( $\alpha$  and *C* are constants). By changing *x* and  $\delta$ , we have successfully excluded the contribution of Cu-O chains in  $\mu_H^{-1}$ , and shown that  $\alpha$  is essentially independent of doping level and disorder. Moreover, the doping-independent  $\alpha$  is universal in various high- $T_c$  superconducting cuprates, and this indicates that  $\mu_H^{-1}$  is more fundamental than  $R_{ab}^{+1}$ . [S0163-1829(96)02846-9]

In recent solid-state physics, it is one of central issues whether the electronic properties in high- $T_c$  superconducting cuprates (HTSC's) can be understood within the Fermiliquid (FL) theory or not. Among their anomalous properties, normal-state charge transport such as the in-plane resistivity  $\rho_{ab}$  and the in-plane Hall coefficient  $R_{ab}^{H}$  are most strongly against the FL picture,<sup>1</sup> and exhibit complicated dependence on temperature,<sup>2</sup> carrier doping,<sup>3-5</sup> and disorder.<sup>6</sup>

An important finding on the understanding of  $\rho_{ab}$  and  $R_{ab}^{H}$ is that the cotangent of the Hall angle,  $\cot \theta_H \equiv \rho_{ab}/HR_{ab}^{H} \equiv \mu_H^{-1}/H$  is expressed as  $\cot \theta_H = \alpha T^2 + C$  ( $\alpha$  and *C* are constants), which is valid in all the *p*-type HTSC's with various carrier<sup>3,8-10</sup> and impurity<sup>6,9,11</sup> concentrations. This naturally indicates that  $\cot \theta_H$  (or  $\mu_H$ ) is more fundamental than  $R_{ab}^{H}$ , and thus it will be a clue for selecting HTSC theories to make clear which is fundamental. However, there is no consensus on  $\cot \theta_H$  or  $\mu_H$ . For example, the doping dependence of  $\cot \theta_H$  in YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7- $\delta$ </sub> (YBCO) is controversial,<sup>8-10</sup> which might arise from the conducting Cu-O chains.<sup>4,12</sup>

We recently reported the transport properties of *c*-axisoriented  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  ( $x \le 0.5$ ) thin films.<sup>13</sup> The heavy Ca doping level up to 0.5 makes it possible to dope carriers into YBCO without filling the oxygen deficiency, and thus  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films are more effective than untwinned YBCO crystals.<sup>14</sup> In this paper,  $\rho_{ab}$ ,  $R_{ab}^H$ , and  $\cot\theta_H$  of  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films have been systematically investigated. The Cu-O chain contributions have been successfully eliminated from  $\cot\theta_H$ , and it has been revealed that  $\alpha$  is independent of the carrier-doping level and the disorder. Moreover, as comparing  $\alpha$  among the HTSC's, the *T*-dependent part of  $\mu_H^{-1}$  is found to be independent of the species of HTSC's, which strongly suggests that  $\mu_H^{-1}$  is more fundamental than  $R_{ab}^{H}$ .

 $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films with a typical thickness of 2000 Å were deposited onto SrTiO<sub>3</sub> single-crystal substrates by RF thermal plasma deposition technique.<sup>13</sup> The as-grown samples were post-annealed under different thermal conditions to control the oxygen content. X-ray diffraction and transmission electron microscopy (TEM) showed that *c*-axisoriented  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  was grown without any impurity phases. The Raman spectroscopy measurement revealed that the doped Ca mainly occupied the Y site. dc resistivity was measured using a standard four-probe method and Hall

coefficient was measured in a magnetic field of 8 T parallel to the *c* axis. In order to eliminate the zero-field signal due to the misalignment of voltage contacts, we rotated the samples by 180° in a static field. The oxygen deficiency  $\delta$ was estimated by the following procedure. First the hole concentration per Cu, *p*, was evaluated from the value of  $T_c$  using the previously reported parabolic curve  $T_c/T_{c,\max}=1-82.6(p-0.16)^{2.15}$  Next,  $\delta$  was estimated using the relationship  $p=p(\delta)$  obtained from the measurements of  $T_c$  and the thermoelectric power, and the calculation of bond-valence sum for  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  by Tallon *et al.*<sup>16</sup>

Figures 1(a) and 1(b) show the temperature dependence of  $\rho_{ab}$  and  $R_{ab}^{H}$  for  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  (x=0 and 0.5) thin films, respectively. First of all, we emphasize that the data



FIG. 1. Temperature dependence of (a) in-plane resistivity  $\rho_{ab}$  and (b) Hall coefficient  $R_{ab}^{H}$ , for  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films with various  $\delta$ . The broken and solid curves are for x=0 and x=0.5, respectively.

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FIG. 2.  $T^2$  dependence of  $\cot \theta_H \ (\equiv \rho_{ab}/HR_{ab}^H)$  in 8 T for  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films. (a) for x=0, 0.5, and  $\delta \ge 0.5$ ; (b) for  $0 \le x \le 0.5$  and  $\delta < 0.5$ . The broken curves, open circles, closed squares, and solid curves correspond to x=0, 0.1, 0.3, and 0.5, respectively. Note that the right axis is the inverse of Hall mobilities.

for x=0 shown by the dotted curves are essentially identical to those for high-quality single crystals.<sup>4</sup> For example, the  $YBa_2Cu_3O_{6.92}$  film shows the *T*-linear resistivity with a small residual resistivity, and shows a superconducting transition at 92 K with a reasonably sharp transition width of 1 K. These results well guarantee the quality of our samples, and consequently we think that the data for x=0.5 films reflect the intrinsic nature of  $Y_{0.5}Ca_{0.5}Ba_2Cu_3O_{7-\delta}$ . Moreover, in Ref. 13, it has been clarified that the crystallinity of the x=0.5 film is as high as that of x=0 film from TEM measurement. In the x = 0.5 films, the doping level is varied from the under- to overdoped regions by changing  $\delta$  from 1.0 down to 0.57. With decreasing  $\delta$ ,  $\rho_{ab}$ , and  $R_{ab}^{H}$  for x=0.5shown by the solid curves in Fig. 1 monotonically decrease, indicating that the carriers are continuously doped. In addition, the  $T_c$  of the x=0.5 films takes a maximum near  $\delta$ =0.72 and reduces with decreasing  $\delta$ . We emphasize that the optimally doped x=0.5 film ( $\delta \sim 0.72$ ) has  $\rho_{ab}$  as low as YBCO<sub>7</sub>, from which the mean-free path is calculated to be 21 Å at 300 K.<sup>17</sup> This indicates 50% Ca substitution does not disturb the in-plane conduction seriously.

The temperature dependence of  $\cot \theta_H$  calculated from  $\rho_{ab}$ and  $R_{ab}^H$  in Fig. 1 is plotted as a function of  $T^2$  in Fig. 2, where  $\cot \theta_H$  in all the samples roughly satisfies the relation of  $\cot \theta_H = \alpha T^2 + C$ . Note that the data for  $\delta \ge 0.5$  are shown in Fig. 2(a), while the data for  $\delta < 0.5$  are in Fig. 2(b) with the data for x=0.1 and x=0.3 newly added. Most unexpectedly, all the x=0.5 samples show the identical  $\cot \theta_H - T^2$  curves, i.e., both  $\alpha$  and C are independent of  $\delta$ . The  $\delta$ -independent Cmeans that the oxygen depletion does not introduce disorder into the CuO<sub>2</sub> plane, while the  $\delta$ -independent  $\alpha$  indicates that



FIG. 3. The slope  $\alpha$  of  $\cot \theta_H = \alpha T^2 + C$  curve for  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  ( $0 \le x \le 0.5$ ) thin films as a function of  $\delta$ . Closed circles, closed squares, closed triangles, open circles, and open squares are for x=0, 0.1, 0.3, 0.4, and 0.5, respectively. The solid curve is the guide for the eyes. Inset shows the zero-temperature-intercept *C* as a function of *x*.

the carrier doping hardly affects  $\alpha$  in Y<sub>0.5</sub>Ca<sub>0.5</sub>Ba<sub>2</sub>Cu<sub>3</sub>O<sub>7- $\delta$ </sub>. We further note that  $\alpha$  for Y<sub>0.5</sub>Ca<sub>0.5</sub>Ba<sub>2</sub>Cu<sub>3</sub>O<sub>7- $\delta$ </sub> is almost equal to that for YBa<sub>2</sub>Cu<sub>3</sub>O<sub>6.48</sub>. On the contrary, as shown in Fig. 2(b), the Ca substitution causes a decrease in  $\alpha$  accompanied by an increase in *C*.

To see the doping dependence of  $\alpha$  and C more clearly, we plotted  $\alpha$  as a function of  $\delta$ , and C as a function of x in Fig. 3. The Ca substitution introduces disorder into the  $CuO_2$ plane, and thus C monotonically increases with x, whereas  $\alpha$ is independent of x and increases with decreasing  $\delta$  only for  $\delta < 0.5$ . We think that the large  $\alpha$  in the  $\delta \sim 0$  samples arises from the conducting Cu-O chains. Reflecting the onedimensional nature, the Cu-O chains are expected to give no Hall voltage. In addition, in real experimental situations, Hall bars electronically short the CuO<sub>2</sub> plane to the Cu-O chain, which force us to reduce the Hall voltage in the plane to that in the chain.<sup>18</sup> The fact that YBa<sub>2</sub>Cu<sub>4</sub>O<sub>8</sub> with conducting Cu-O double chains shows unusually small  $R_{ab}^{H}$  (Ref. 19) evidences our interpretation. Accordingly, the  $\delta$ -independent  $\alpha$  for  $\delta \ge 0.5$ , where the Cu-O chains are no longer conductive, can be regarded as the intrinsic value to the  $CuO_2$  plane in YBCO.

Since we have shown that the slope  $\alpha$  inherent in the CuO<sub>2</sub> plane in YBCO is independent of carrier concentration and disorder, let us now compare  $\mu_H^{-1}$  for YBCO with that for other HTSC's. We have selected the data to be compared on the basis of following criteria. (i)  $\mu_H^{-1}$  should be measured using high-quality single crystals, because resistivity is usually one order of magnitude larger in polycrystals than in single crystals. (ii) Overdoped La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> should be excluded as an exception. La-Sr-Cu-O is the only *p*-type cuprate whose  $R_{ab}^{H}$  changes its sign in the overdoped region, and thus  $\mu_H^{-1}$  diverges when  $R_{ab}^{H} \sim 0.^{20,21}$ 

Figure 4 shows thus selected  $\mu_H^{-1}$  as a function of  $T^2$  for various HTSC's (Refs. 3, 5, 22, and 23), where the *T*-dependent part in  $\mu_H^{-1}$  suprisingly coincides among all the data. It is our claim in the present paper that the *T*-dependent part in  $\mu_H^{-1}$  is universal regardless of carrier concentration, disorder, and class of HTSC's.



FIG. 4. The comparison of the inverse Hall mobility  $\mu_H^{-1}$  as a function of  $T^2$  for various HTSC's. The solid curve and broken curve are for the present  $Y_{0.5}Ca_{0.5}Ba_2Cu_3O_{6.38}$  and  $YBa_2Cu_3O_{6.48}$  thin films, respectively. The open triangles and closed circles are for the data of  $La_{2-x}Sr_xCuO_4$  with x=0.1 and 0.15, respectively (Ref. 5). The open squares, closed triangles, and open circles are for the data of  $Bi_2Sr_2CaCu_2O_8$  (Ref. 22), TlBa\_2CuO\_{6+\delta} (Ref. 3), and HgBa\_2Ca\_2Cu\_3O\_{8+\delta} (Ref. 23), respectively.

Here we will consider the physical meaning of the universal T dependence in  $\mu_H^{-1}$  qualitatively. We can point out many facts implying that  $\mu_H^{-1}$  is related to fermion-fermion scattering. First, the *T*-dependent part in  $\mu_H^{-1}$  is roughly proportional to  $T^2$ , which reminds us of electron-electron scattering. Second, the doping independence in  $\mu_H^{-1}$  suggests that  $\mu_H^{-1}$  is associated with 1-p, that is, the large Fermi surface predicted by the band calculation. Third, the remarkable difference in  $\mu_H^{-1}$  between overdoped La-Sr-Cu-O and other HTSC's is attributed to the different shapes of the Fermi surface; the band theory has predicted that the Fermi surface in La-Sr-Cu-O goes from open to close with carrier doping,<sup>24</sup> whereas that in other HTSC's remains open.<sup>25–27</sup> Taking these facts into account, we suggest that the universal  $\mu_{H}^{-1}$  is a direct probe for the uncorrelated Fermi surface. Note that, even in non-Fermi liquids, the shape of the Fermi surface will more or less influence the electronic properties. As long as elementary excitations derived from electrons are fermions, any properties related to the Fermi-Dirac statistics will remain unchanged. For example, the Fermi surface of electrons survives as the Fermi surface of spinons in the resonating-valence-bond (RVB) theory, as suggested by Tanamoto, Kohno, and Fukuyama.<sup>28</sup> From the viewpoint of the RVB theory,  $\mu_H^{-1}$  is related to spinon-spinon scattering proposed by Anderson,<sup>7</sup> which is expected to coincide with the electron-electron scattering in the overdoped HTSC's.

- \*Present address: Tokyo Gas Co., Ltd., 1-7-7, Suehiro-cho, Tsurumi-ku, Yokohama, 230, Japan.
- <sup>†</sup>Present address: The Furukawa Electric Co., Ltd., 5-1-9, Higashi-Yawata, Hiratsuka, 254, Japan.
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Finally we will comment on the theories<sup>3,7,22,29,30,31</sup> explaining the  $T^2$  dependence of  $\mu_H^{-1}$  briefly. Our results clearly indicate that  $\mu_H^{-1}$  is more fundamental than  $\rho_{ab}$  or  $R_{ab}^{H}$ , and hence any theories giving explicit expressions to  $\rho_{ab}$  and  $R_{ab}^{H}$  separately are unlikely to explain the universal  $\mu_H^{-1}$ . It is very hard to believe that  $\rho_{ab}$  or  $R_{ab}^H$ , which change with doping and disorder in a complicated way, accidentally keep  $\rho_{ab}/R_{ab}^{H}$  unchanged. After such theories are ruled out, there remain only two possibilities, to our knowledge: one is proposed by Anderson<sup>7</sup> and the other is suggested independently by Kendziora et al.<sup>22</sup> and Carrington et al.<sup>29</sup> on the basis of FL. Both explanations assume two kinds of scattering times.  $\mu_H^{-1}$  is attributed to spinon-spinon scattering in the former, while it is assigned to the scattering at the corner of the rounded-square-shaped Fermi surface in the latter. Although the present data are still insufficient to choose either of the two as a correct answer, we expect that the T dependence of  $\rho_{ab}$  is difficult to explain within a FL picture. For example,  $\rho_{ab}$  for x=0.5 and  $\delta$ =1.0 is slightly sublinear as a function of T, and the T-dependent part in  $\rho_{ab}$  for x=0.5 and  $\delta \leq 0.72$  is not proportional to  $T^2$ . In other words,  $\rho_{ab}$  for x=0.5 films does not show a typical T dependence for HTSC's, possibly owing to the highly disordered CuO<sub>2</sub> plane induced by the 50 at. % substitution of Ca for Y. These results suggest that conventional Matthiessen's rule expected in a FL picture is seriously violated. For the elucidation of the physical meaning of the universal  $\mu_H^{-1}$  and the effect of disorder on  $\rho_{ab}$ , further quantitative studies are necessary both experimentally and theoretically.

In summary, the transport properties of  $Y_{1-x}Ca_xBa_2Cu_3O_{7-\delta}$  thin films with a wide range of x=0.0-0.5 and  $\delta=0.08-1.0$  have been systematically studied. For all the samples, the *T*-dependent part of  $\mu_H^{-1}$  is roughly proportional to  $T^2$ . By changing *x* and  $\delta$ , we have successfully extracted the inherent element of the CuO<sub>2</sub> planes in  $\mu_H^{-1}$ , and shown that the *T*-dependent part of  $\mu_H^{-1}$  is essentially independent of doping level and disorder. We have further found that the *T*-dependent part in  $\mu_H^{-1}$  is universal in various HTSC's, which strongly suggests that  $\mu_H^{-1}$  is more fundamental than  $R_{ab}^{H}$ , and the existence of two kinds of scattering times.

We would like to thank T. Machi for helpful discussions, J. G. Wen for TEM measurements, and N. Watanabe for Raman measurements. This work was partially supported by the New Energy and Industrial Technology Development Organization for the R&D of Industrial Science and Technology Frontier Program.

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- <sup>18</sup>This is the same situation as Hall bars too close to a current pad giving a smaller voltage than the intrinsic value; In a two-band model with a two-dimensional plane band and a onedimensional chain band, assuming  $\rho_{\rm pl} \approx \rho_{\rm ch}$ , one can obtain  $\cot \theta_{\rm tw} = 4/3 \cot \theta_{\rm pl}$ , where  $\cot \theta_{\rm tw}$  is the Hall angle for a twinned crystal and  $\cot \theta_{\rm pl}$  is the Hall angle inherent in the CuO<sub>2</sub> plane. Thus, the increase of  $\alpha$  with decreasing  $\delta$  is also explainable with the two-band model. In our real observation, however, the

increase of  $\alpha$  is larger than the calculated one.

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